



.

#### **DUAL P-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on) max</sub>	<b>Ι</b> <sub>D</sub> Τ <sub>A</sub> = +25°C
-50V	10Ω @ V <sub>GS</sub> = -5V	-130mA

#### Description

This MOSFET has been designed to minimize the on-state resistance  $(R_{DS(on)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### Applications

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

## SOT363



Top View

Low On-Resistance

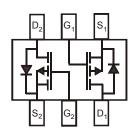
Low Gate Threshold Voltage

Features and Benefits

- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: SOT363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)



Top View Internal Schematic

### Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
BSS84DW-7-F	Standard	SOT363	3,000/Tape & Reel
BSS84DWQ-13	Automotive	SOT363	10,000/Tape & Reel
BSS84DWQ-7	Automotive	SOT363	3,000/Tape & Reel

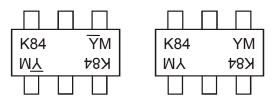
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

### **Marking Information**



K84 = Product Type Marking Code YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)  $\overline{YM} = Date Code Marking for CAT (Chengdu Assembly/ Test site)$ Y or  $\overline{Y}$  = Year (ex: A = 2013) M = Month (ex: 9 = September)

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	К	L	М	Ν	Р	R	S	Т	U	V	W	Х	Y	Z
Month	Jan	Fe	b I	Mar	Apr	Мау	Ju	n	Jul	Aug	Sep	Oc	t I	Nov	Dec
Code	1	2		3	4	5	6		7	8	9	0		Ν	D



## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V <sub>DSS</sub>	-50	V
Drain-Gate Voltage (Note 5)		V <sub>DGR</sub>	-50	V
Gate-Source Voltage	Continuous	V <sub>GSS</sub>	±20	V
Drain Current (Note 6)	Continuous	I <sub>D</sub>	-130	mA

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 6)	PD	300	mW
Thermal Resistance, Junction to Ambient	R <sub>0JA</sub>	417	°C/W
Operating and Storage Temperature Range	TJ, T <sub>STG</sub>	-55 to +150	°C

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						·
Drain-Source Breakdown Voltage	<b>BV</b> <sub>DSS</sub>	-50	-75		V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250µA
			_	-1	μA	V <sub>DS</sub> = -50V, V <sub>GS</sub> = 0V, T <sub>J</sub> = +25°C
Zero Gate Voltage Drain Current	Inno	_	_	-2		V <sub>DS</sub> = -50V, V <sub>GS</sub> = 0V, T <sub>J</sub> = +125°C
	IDSS	_		-100	nA	V <sub>DS</sub> = -25V, V <sub>GS</sub> = 0V, T <sub>J</sub> = +25°C
Gate-Body Leakage	Igss	_		±10	nA	$V_{GS}$ = ±20V, $V_{DS}$ = 0V
ON CHARACTERISTICS (Note 7)				÷		
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.8	-1.6	-2.0	V	$V_{DS} = V_{GS}$ , $I_D = -1mA$
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	_	6	10	Ω	V <sub>GS</sub> = -5V, I <sub>D</sub> = -0.100A
Forward Transconductance	<b>g</b> fs	0.05	_		S	V <sub>DS</sub> = -25V, I <sub>D</sub> = -0.1A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C <sub>iss</sub>	_	_	45	pF	
Output Capacitance	Coss	_	_	25	pF	V <sub>DS</sub> = -25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>		_	12	pF	
SWITCHING CHARACTERISTICS	•			•	•	•
Turn-On Delay Time	t <sub>D(ON)</sub>	_	10		ns	V <sub>DD</sub> = -30V, I <sub>D</sub> = -0.27A,
Turn-Off Delay Time	t <sub>D(OFF)</sub>		18		ns	$R_{GEN} = 50\Omega$ , $V_{GS} = -10V$

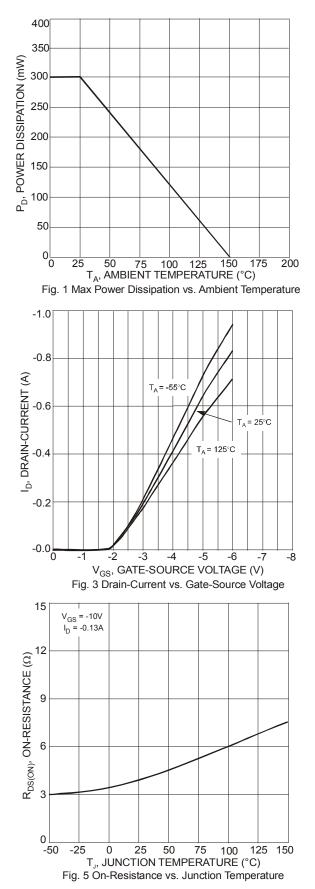
Notes: 5.  $R_{GS} \le 20 K \Omega$ .

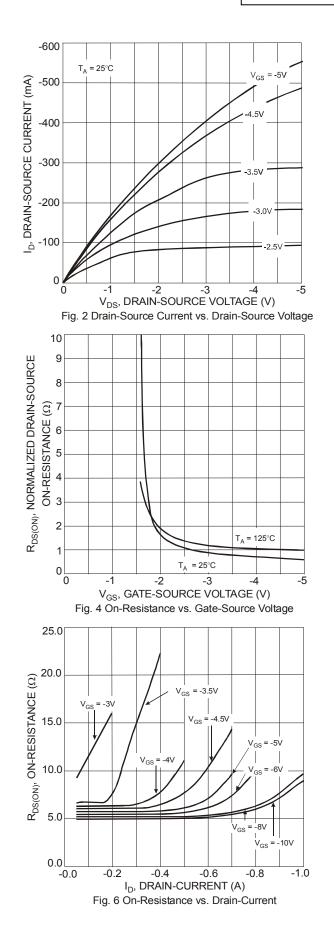
6. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001,

which can be found on our website at http://www.diodes.com.

7. Short duration pulse test used to minimize self-heating effect.



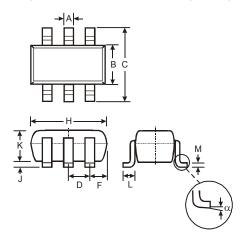






### **Package Outline Dimensions**

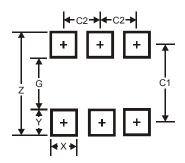
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SC	DT363	
Dim	Min	Max	Тур
Α	0.10	0.30	0.25
в	1.15	1.35	1.30
с	2.00	2.20	2.10
D		0.65 Ty	р
F	0.40	0.45	0.425
Н	1.80	2.20	2.15
J	0	0.10	0.05
κ	0.90	1.00	1.00
L	0.25	0.40	0.30
М	0.10	0.22	0.11
α	0°	8°	-
All	Dimen	isions i	n mm

### Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65



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